

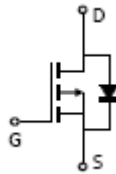
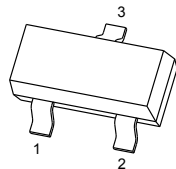
FEATURE

- High density cell design for low $R_{DS(ON)}$
- Voltage controlled small signal switch
- Rugged and reliable
- High saturation current capability

SOT-23

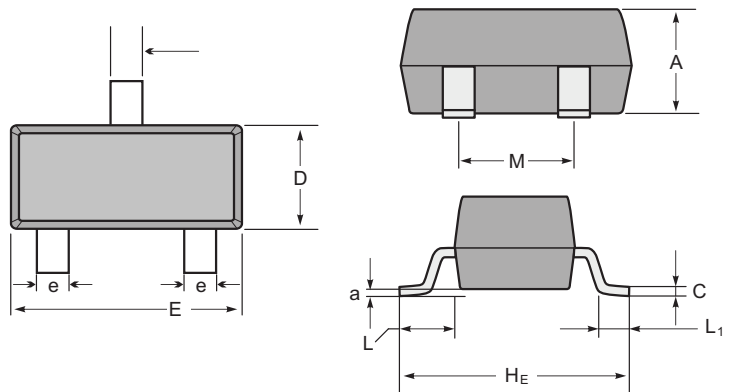
1. GATE
2. SOURCE
3. DRAIN

Equivalent Circuit



Marking

Type number	Marking code
AO3407	A79T



SOT-23 mechanical data

UNIT		A	C	D	E	H _E	e	M	L	L ₁	a
mm	max	1.1	0.15	1.4	3.0	2.6	0.5	1.95	0.55 (ref)	0.36 (ref)	0.0
	min	0.9	0.08	1.2	2.8	2.2	0.3	1.7			0.15
mil	max	43	6	55	118	102	20	77	22 (ref)	14 (ref)	0.0
	min	35	3	47	110	87	12	67			6

Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	-4.1	A
Drain Current-Pulsed (Note 1)	I_{DM}	-20	A
Maximum Power Dissipation	P_D	1.2	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^{\circ}\text{C}$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	90	$^{\circ}\text{C/W}$
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AO3407

Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-30	-33	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-24V, V_{GS}=0V$	-	-	-1	μA

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =-250μA	-1	-1.5	-3	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-10V, I _D =-4.1A	-	48	65	mΩ
		V _{GS} =-4.5V, I _D =-4A	-	60	95	mΩ
Forward Transconductance	g _{FS}	V _{DS} =-5V,I _D =-4.1A	5.5	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{iss}	V _{DS} =-15V,V _{GS} =0V, F=1.0MHz	-	650	-	PF
Output Capacitance	C _{oss}		-	105	-	PF
Reverse Transfer Capacitance	C _{rss}		-	65	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =-15V,R _L =3.6Ω V _{GS} =-10V,R _{GEN} =3Ω	-	8.5	-	nS
Turn-on Rise Time	t _r		-	4.5	-	nS
Turn-Off Delay Time	t _{d(off)}		-	26	-	nS
Turn-Off Fall Time	t _f		-	12.5	-	nS
Total Gate Charge	Q _g	V _{DS} =-15V,I _D =-4A,V _{GS} =-10V	-	12.5	-	nC
Gate-Source Charge	Q _{gs}		-	2.8	-	nC
Gate-Drain Charge	Q _{gd}		-	2.7	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =-4.1A	-	-	-1.2	V

RATING AND CHARACTERISTIC CURVES (AO3407)

Figure 1: Switching Test Circuit

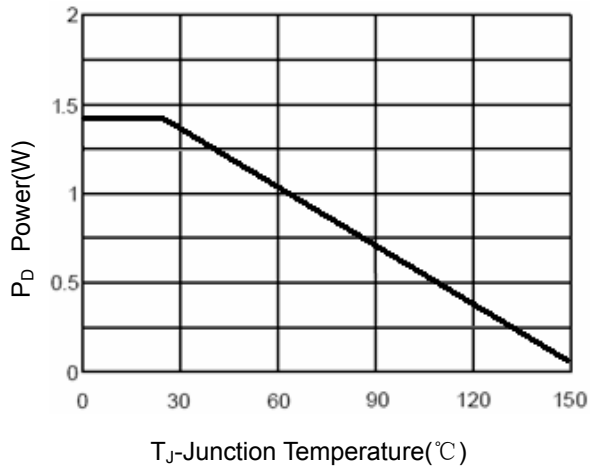


Figure 3 Power Dissipation

Figure 2: Switching Waveforms

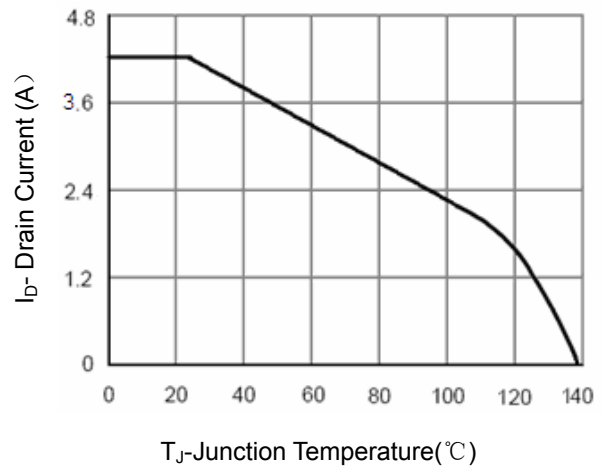


Figure 4 Drain Current

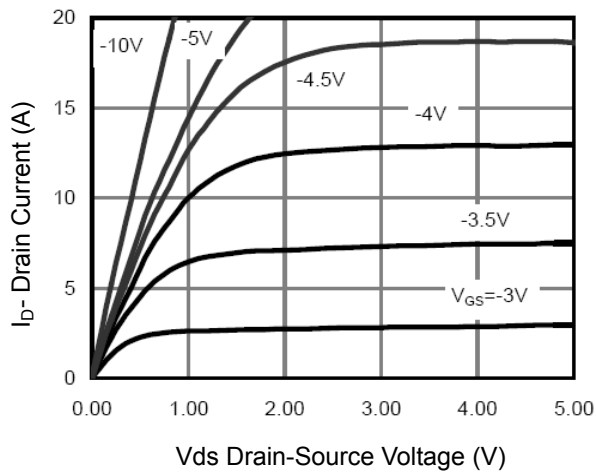


Figure 5 Output Characteristics

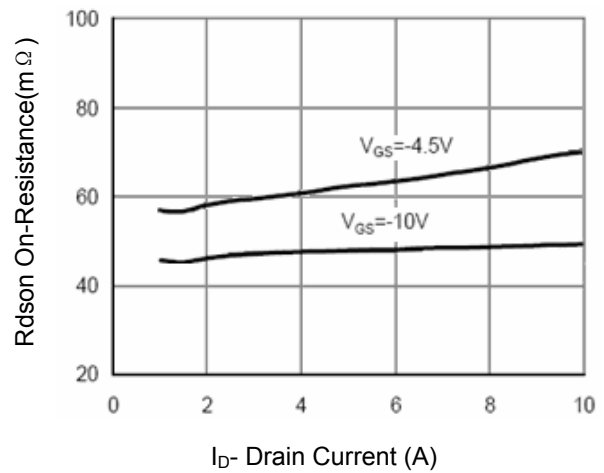


Figure 6 Drain-Source On-Resistance

RATING AND CHARACTERISTIC CURVES (AO3407)

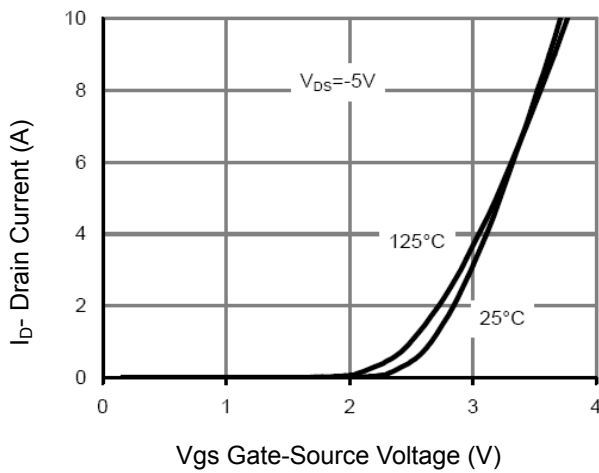


Figure 7 Transfer Characteristics

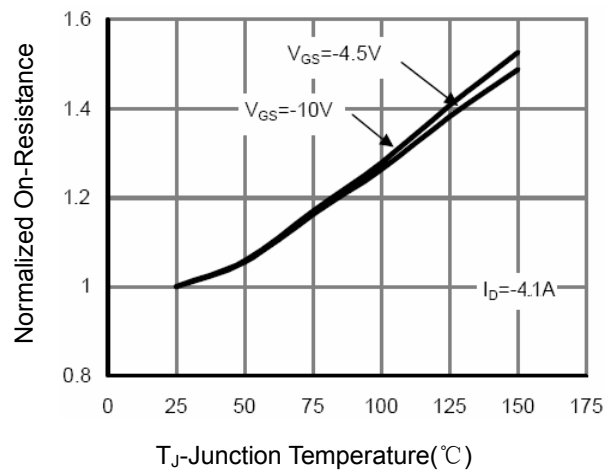


Figure 8 Drain-Source On-Resistance

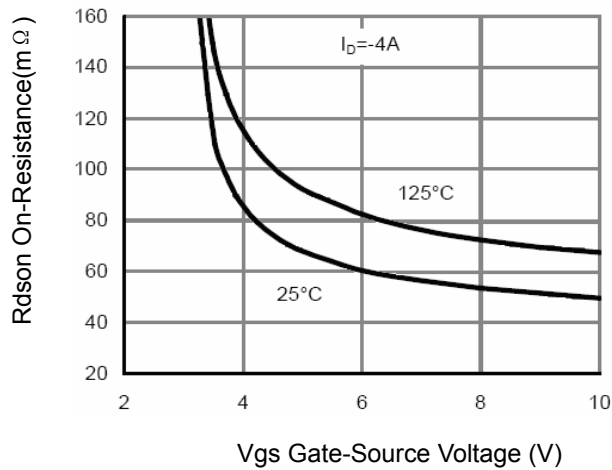


Figure 9 Rdson vs Vgs

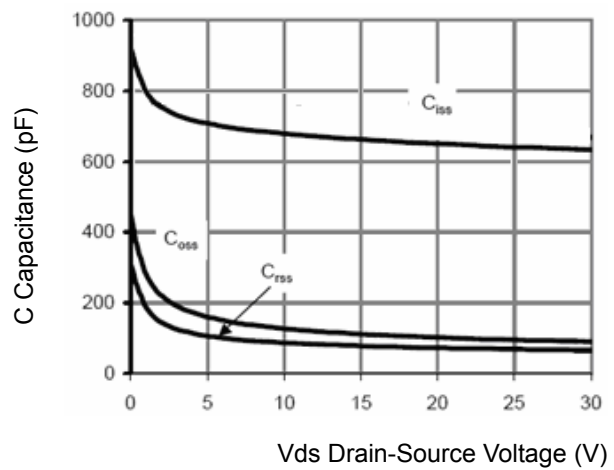


Figure 10 Capacitance vs Vds

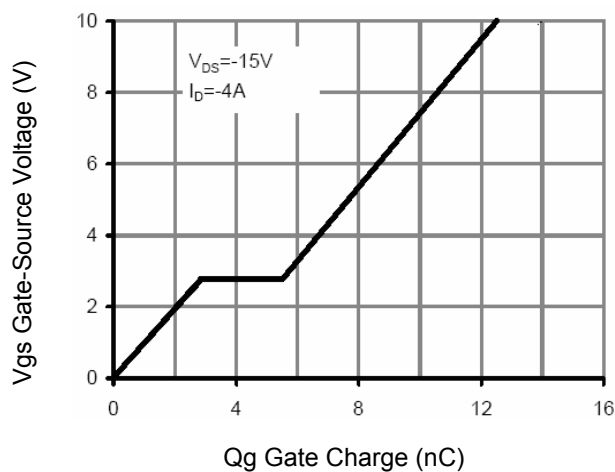


Figure 11 Gate Charge

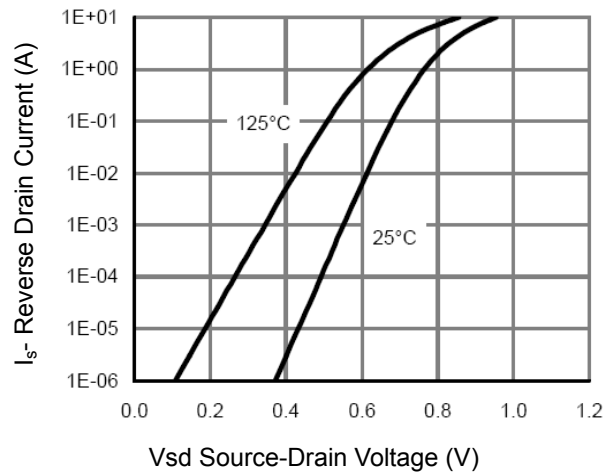


Figure 12 Source- Drain Diode Forward